

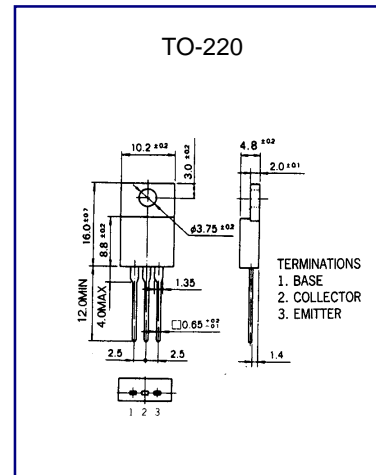


**2SB834**

**NPN EPITAXIAL SILICON TRANSISTOR**

**LOW FREQUENCY POWER AMPLIFIER**

- Complement to 2SD880



**ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-60	V
Collector-Emitter Voltage	VCEO	-60	V
Emitter-Base voltage	VEBO	-7	V
Collector Current (DC)	IC	-3	A
Collector Dissipation(Tc=25°C)	PC	30	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-50~150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	VCB= -60V , IE=0			-100	μA
Emitter Cutoff Current	IEBO	VEB= -7V, IC=0			-100	μA
DC Current Gain	hFE1	VCE= -5V, IC=-0.5A	60		300	
DC Current Gain	hFE2	VCE= -5V, IC=-3A	20			
Collector- Emitter Saturation Voltage	VCE(sat)	IC=-3A , IB=-0.3A		-0.4	-1.0	V
Current Gain Bandwidth Product	fT	VCE= -5V , IC=-0.5A		9		MHZ